

RGCL60TS60

600V 30A Field Stop Trench IGBT

V _{CES}	600V
I _{C(100°C)}	30A
V _{CE(sat) (Typ.)}	1.4V
P_D	111W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Soft Switching
- 3) Pb free Lead Plating; RoHS Compliant

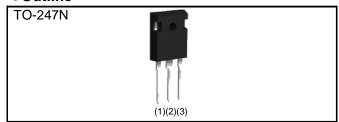
Applications

Partial Switching PFC

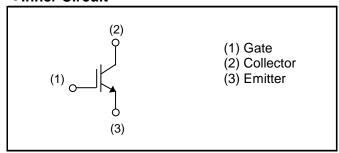
Discharge Circuit

Brake for Inverter

Outline



●Inner Circuit



Packaging Specifications

		
Туре	Packaging	Tube
	Reel Size (mm)	-
	Tape Width (mm)	-
	Basic Ordering Unit (pcs)	450
	Taping Code	C11
	Marking	RGCL60TS60

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit	
Collector - Emitter Voltage		V_{CES}	600	V	
Gate - Emitter Voltage		V_{GES}	±30	V	
Collector Current	T _C = 25°C	I _C	48	А	
	T _C = 100°C	I _C 30		А	
Pulsed Collector Current		I _{CP} *1	120	А	
Power Dissipation	$T_C = 25^{\circ}C$	P_{D}	111	W	
	T _C = 100°C	P_{D}	55	W	
Operating Junction Temperature		T _j	-40 to +175	°C	
Storage Temperature		T _{stg}	-55 to +175	°C	

^{*1} Pulse width limited by T_{jmax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	1.34	°C/W

ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Symbol	Conditions	Values			Unit
		Min.	Тур.	Max.	Uniil
BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	600	1	-	V
I _{CES}	$V_{CE} = 600V, V_{GE} = 0V$	1	1	10	μΑ
I _{GES}	$V_{GE} = \pm 30V$, $V_{CE} = 0V$		-	±200	nA
$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 18.9 \text{mA}$	4.5	5.5	6.5	V
	$I_C = 30A, V_{GE} = 15V$				
V _{CE(sat)}	T _j = 25°C	-	1.4	1.8	V
	T _j = 175°C	-	1.6	-	
	BV _{CES} I _{CES} V _{GE(th)}	BV _{CES} $I_C = 10\mu A$, $V_{GE} = 0V$ $I_{CES} V_{CE} = 600V, V_{GE} = 0V$ $I_{GES} V_{GE} = \pm 30V, V_{CE} = 0V$ $V_{GE(th)} V_{CE} = 5V, I_C = 18.9mA$	$BV_{CES} I_C = 10 \mu A, \ V_{GE} = 0V \qquad 600$ $I_{CES} V_{CE} = 600 V, \ V_{GE} = 0V \qquad -$ $I_{GES} V_{GE} = \pm 30 V, \ V_{CE} = 0V \qquad -$ $V_{GE(th)} V_{CE} = 5 V, \ I_C = 18.9 mA \qquad 4.5$ $I_C = 30 A, \ V_{GE} = 15 V$		

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Doromotor	Cumbal	Conditions	Values			l loit
Parameter	Symbol		Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1600	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	38	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	29	-	
Total Gate Charge	Q_g	V _{CE} = 300V	-	68	-	
Gate - Emitter Charge	Q_{ge}	I _C = 30A	-	13	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	27	-	•
Turn - on Delay Time	t _{d(on)}	$I_C = 30A, V_{CC} = 400V$	-	44	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	27	-	na
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	186	-	ns
Fall Time	t _f	Inductive Load	-	178	-	
Turn - on Switching Loss	E _{on}	*Eon includes diode	-	0.77	-	
Turn - off Switching Loss	E _{off}	reverse recovery	-	1.11	-	mJ
Turn - on Delay Time	t _{d(on)}	$I_C = 30A, V_{CC} = 400V$	-	40	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	45	-	na
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	207	-	ns
Fall Time	t _f	Inductive Load	-	272	-	
Turn - on Switching Loss	E _{on}	*Eon includes diode	-	0.97	-	
Turn - off Switching Loss	E _{off}	reverse recovery	-	1.54	-	mJ
		$I_C = 120A, V_{CC} = 480V$				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 600V, V_{GE} = 15V$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Fig.1 Power Dissipation vs. Case Temperature

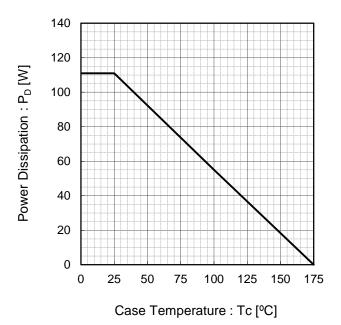


Fig.2 Collector Current vs. Case Temperature

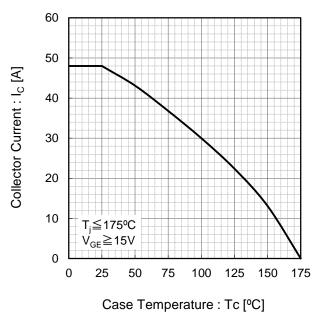


Fig.3 Forward Bias Safe Operating Area

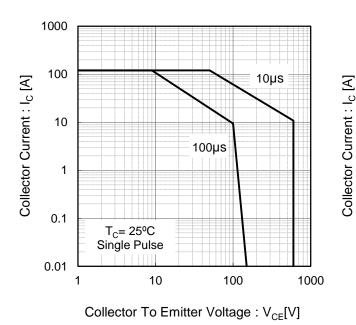


Fig.4 Reverse Bias Safe Operating Area

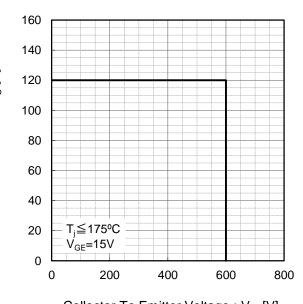


Fig.5 Typical Output Characteristics

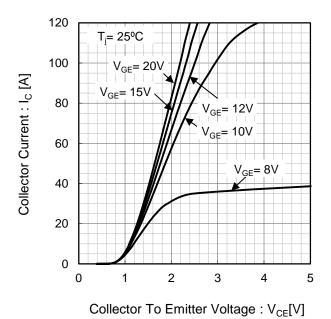
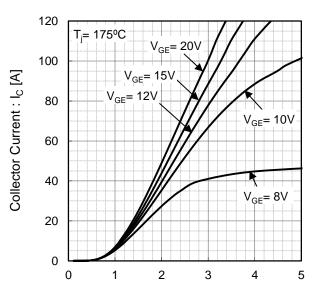


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V_{CE}[V]

Fig.7 Typical Transfer Characteristics

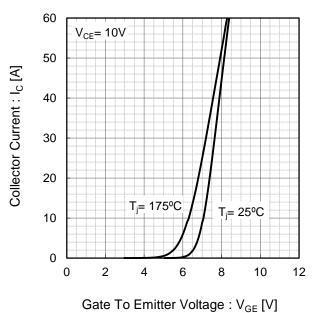
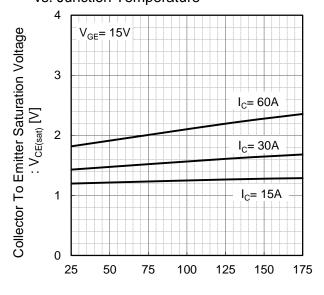
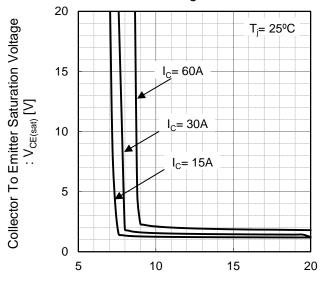


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



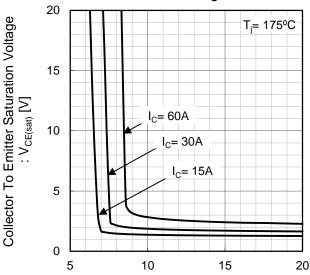
Junction Temperature : T_i [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

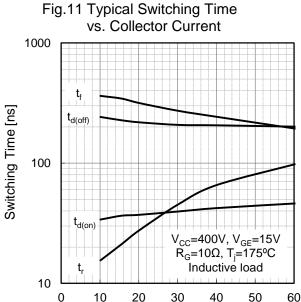


Gate To Emitter Voltage : V_{GE} [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage: V_{GE} [V]



Collector Current : I_C [A]

60

Fig.12 Typical Switching Time vs. Gate Resistance 1000 Switching Time [ns] t_{d(off)} 100 $t_{d(on)}$ $V_{\rm CC}$ =400V, $I_{\rm C}$ =30A $V_{\rm GE}$ =15V, $T_{\rm j}$ =175°C Inductive load 10 0 10 20 30 40 50

Gate Resistance : $R_G[\Omega]$

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{o}\mathsf{n}}$ 0.1 V_{CC} =400V, V_{GE} =15V R_{G} =10 Ω , T_{j} =175°C Inductive load 0.01 10 20 30 40 50 60 0 Collector Current : I_C [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] $\mathsf{E}_{\mathsf{off}}$ 1 E_{on} 0.1 V_{CC} =400V, I_{C} =30A V_{GE} =15V, T_{j} =175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] 100 Coes Cres 10 f=1MHz $V_{GE}=0V$ T_i=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE}[V]

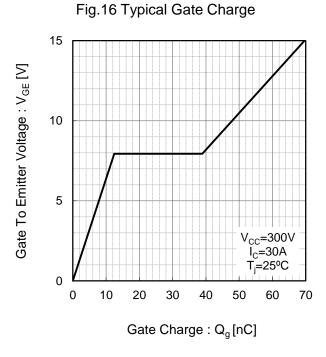
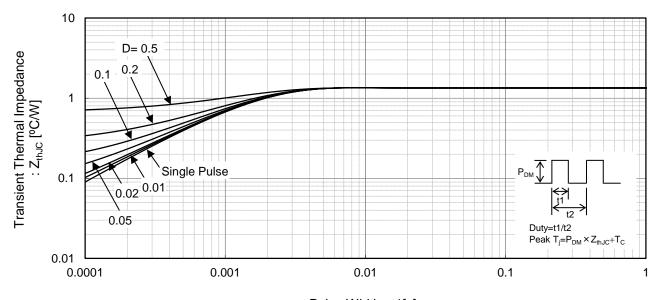


Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

●Inductive Load Switching Circuit and Waveform

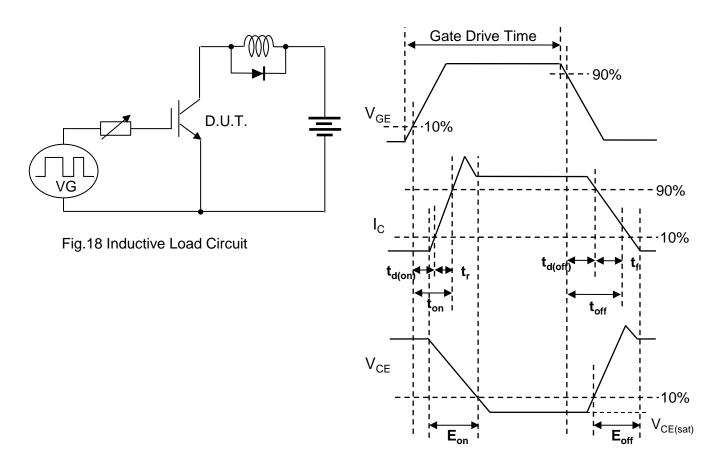


Fig.19 Inductive Load Waveform

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